

AMENDMENTS TO THE CLAIMS:

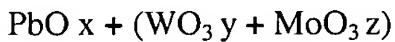
This listing of claims will replace all prior versions, and listings, of claims in the application:

1.-3. Canceled.

4. (Currently Amended) A method, for producing the low-temperature sintered dielectric ceramic material of claim 4 having a composition of ABO_3 dielectric ceramic material where a 0.9 molar ratio or more lead is included in site A assuming the proportion of site B is 1, and at least one of tungsten and molybdenum is included, wherein the density of the dielectric ceramic material, after sintering, is 7.5 g/cm^3 or larger, and the combined content of tungsten and molybdenum is less than 0.098 mole to 1 mole of lead,

which method comprises ~~using~~

(1) preparing an auxiliary oxide ~~is used~~ that is made by adding the oxide of at least one of tungsten and molybdenum to lead oxide in proportion of:



where $x + y + z = 1$, $0.005 < y + z < 0.4$ and $y, z \geq 0$;

(2) adding 0.05 mol % to 206 mol % of said auxiliary oxide prepared in step (1) to a mixture of a stock material of low-temperature sintered dielectric ceramic material or calcination thereof that has a composition of ABO_3 type dielectric ceramic material where 0.9 molar ratio or more lead is included in site A assuming the proportion of site B is 1;

(3) mixing the material, followed by

(4) forming and further sintering.

5. (Original) The method for producing the low-temperature sintered dielectric ceramic material according to claim 4, wherein said auxiliary oxide is made by adding the oxide of at least one of tungsten and molybdenum to lead oxide in a dry or a wet mixing process, then processing the mixture through calcination and crushing.

6. (Currently Amended) The method for producing the low-temperature sintered dielectric ceramic material according to claim 4, wherein the quantity of lead included in the stock ~~mixture~~material is set to the required quantity minus the quantity supplied from the lead oxide included in the auxiliary oxide, in ~~the process of~~ preparing the stock ~~mixture~~material to make the dielectric ceramic material.

7. (Currently Amended) The method for producing the low-temperature sintered dielectric ceramic material according to claim 4, wherein said auxiliary oxide used ~~in the production process~~ has melting point in a range from a temperature at which shrinkage ratio of the dielectric ceramic material is 3% to a temperature at which the shrinkage stops.

8. (Currently Amended) The method for producing the low-temperature sintered dielectric ceramic material according to claim 5, wherein a sheet of said dielectric ceramic material made by adding the auxiliary oxide to the stock powder or calcined ~~stock powder, thereof is provided with~~printing an electrode layer ~~printed and~~ laminated thereon ~~with~~and calcining the lamination ~~being calcined at the same time as the sheet is~~calcined.

9.-10. Canceled.

11. (Currently Amended) The method for producing the low-temperature sintered dielectric ceramic material according to claim 5, wherein the quantity of lead included in the stock ~~mixture~~material is set to the required quantity minus the quantity supplied from the lead oxide included in the auxiliary oxide, in ~~the process of~~ preparing the stock ~~mixture~~material to make the dielectric ceramic material.

12. (New) The method for producing the low-temperature sintered dielectric ceramic material according to claim 4, wherein the low-temperature sintered dielectric ceramic material includes lead zirconate titanate as a main component.